

## High speed switching series third generation IGBT

**Maximum Ratings**

For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_{vj} \geq 25^{\circ}\text{C}$	$V_{CE}$	1200	V
DC collector current, limited by $T_{vjmax}$ $T_c = 25^{\circ}\text{C}$ $T_c = 134^{\circ}\text{C}$	$I_C$	150.0 75.0	A
Pulsed collector current, $t_p$ limited by $T_{vjmax}$	$I_{Cpuls}$	300.0	A
Turn off safe operating area $V_{CE} \leq 1200\text{V}$ , $T_{vj} \leq 175^{\circ}\text{C}$ , $t_p = 1\mu\text{s}$	-	300.0	A
Diode forward current, limited by $T_{vjmax}$ $T_c = 25^{\circ}\text{C}$ $T_c = 100^{\circ}\text{C}$	$I_F$	150.0 75.0	A
Diode pulsed current, $t_p$ limited by $T_{vjmax}$	$I_{Fpuls}$	300.0	A
Gate-emitter voltage Transient Gate-emitter voltage ( $t_p \leq 10\mu\text{s}$ , $D < 0.010$ )	$V_{GE}$	$\pm 20$ $\pm 30$	V
Short circuit withstand time $V_{GE} = 15.0\text{V}$ , $V_{CC} \leq 600\text{V}$ Allowed number of short circuits < 1000 Time between short circuits: $\geq 1.0\text{s}$ $T_{vj} = 175^{\circ}\text{C}$	$t_{SC}$	10	$\mu\text{s}$
Power dissipation $T_c = 25^{\circ}\text{C}$ Power dissipation $T_c = 134^{\circ}\text{C}$	$P_{tot}$	938.0 256.0	W
Operating junction temperature	$T_{vj}$	-40...+175	$^{\circ}\text{C}$
Storage temperature	$T_{stg}$	-55...+150	$^{\circ}\text{C}$
Soldering temperature, wave soldering 1.6mm (0.063in.) from case for 10s		260	$^{\circ}\text{C}$

**Thermal Resistance**

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	

**R<sub>th</sub> Characteristics**

IGBT thermal resistance, <sup>1)</sup> junction - case	$R_{th(j-c)}$		-	-	0.16	K/W
Diode thermal resistance, <sup>1)</sup> junction - case	$R_{th(j-c)}$		-	-	0.28	K/W
Thermal resistance junction - ambient	$R_{th(j-a)}$		-	-	40	K/W

<sup>1)</sup> Thermal resistance of thermal grease  $R_{th(c-s)}$  (case to heat sink) of more than 0.1K/W not included.

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Electrical Characteristic, at  $T_{vj} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>Static Characteristic</b>						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0\text{V}, I_C = 0.50\text{mA}$	1200	-	-	V
Collector-emitter saturation voltage	$V_{CEsat}$	$V_{GE} = 15.0\text{V}, I_C = 75.0\text{A}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	- -	2.00 2.50	2.35 -	V
Diode forward voltage	$V_F$	$V_{GE} = 0\text{V}, I_F = 75.0\text{A}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	- -	1.90 1.85	2.30 -	V
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C = 2.60\text{mA}, V_{CE} = V_{GE}$	5.1	5.8	6.5	V
Zero gate voltage collector current	$I_{CES}$	$V_{CE} = 1200\text{V}, V_{GE} = 0\text{V}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	- -	- 5000	450 -	$\mu\text{A}$
Gate-emitter leakage current	$I_{GES}$	$V_{CE} = 0\text{V}, V_{GE} = 20\text{V}$	-	-	100	nA
Transconductance	$g_{fs}$	$V_{CE} = 20\text{V}, I_C = 75.0\text{A}$	-	26.0	-	S

Electrical Characteristic, at  $T_{vj} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>Dynamic Characteristic</b>						
Input capacitance	$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$	-	4856	-	pF
Output capacitance	$C_{oes}$		-	505	-	
Reverse transfer capacitance	$C_{res}$		-	290	-	
Gate charge	$Q_G$	$V_{CC} = 960\text{V}, I_C = 75.0\text{A},$ $V_{GE} = 15\text{V}$	-	370.0	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	$L_E$		-	13.0	-	nH

## Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>IGBT Characteristic, at <math>T_{vj} = 25^{\circ}\text{C}</math></b>						
Turn-on delay time	$t_{d(on)}$	$T_{vj} = 25^{\circ}\text{C},$ $V_{CC} = 600\text{V}, I_C = 75.0\text{A},$ $V_{GE} = 0.0/15.0\text{V},$ $R_{G(on)} = 6.0\Omega, R_{G(off)} = 6.0\Omega,$ $L\sigma = 70\text{nH}, C\sigma = 67\text{pF}$ $L\sigma, C\sigma$ from Fig. E Energy losses include "tail" and diode reverse recovery.	-	38	-	ns
Rise time	$t_r$		-	32	-	ns
Turn-off delay time	$t_{d(off)}$		-	303	-	ns
Fall time	$t_f$		-	32	-	ns
Turn-on energy	$E_{on}$		-	3.40	-	mJ
Turn-off energy	$E_{off}$		-	2.90	-	mJ
Total switching energy	$E_{ts}$		-	6.30	-	mJ